

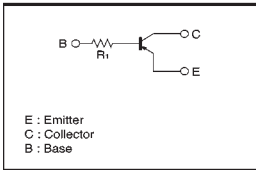
Digital transistor (built-in resistor)

DTA125TUA / DTA125TKA / DTA125TSA

●Features

- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors.
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input, and parasitic effects are almost completely eliminated.
- 3) Only the on / off conditions need to be set for operation, making device design easy.
- 4) Higher mounting densities can be achieved.

●Circuit schematic



●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CB0}	-50	—	—	V	I _C =-50 μA
Collector-emitter breakdown voltage	BV _{CE0}	-50	—	—	V	I _C =-1mA
Emitter-base breakdown voltage	BV _{EB0}	-5	—	—	V	I _E =-50 μA
Collector cutoff current	I _{CB0}	—	—	-0.5	μA	V _{CB} =-50V
Emitter cutoff current	I _{EB0}	—	—	-0.5	μA	V _{EB} =-4V
Collector-emitter saturation voltage	V _{CE(sat)}	—	—	-0.3	V	I _C =-0.5mA, I _E =-0.05mA
DC current transfer ratio	h _{FE}	100	250	600	—	I _C =-1mA, V _{CE} =-5V
Input resistance	R _I	70	100	130	kΩ	—
Transition frequency	f _T	—	250	—	MHz	V _{CE} =-10V, I _E =5mA, f=100MHz *

* Transition frequency of the device.

(94S-552-A125T)

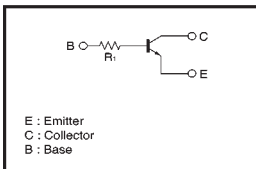
Digital transistor (built-in resistor)

DTC125TUA / DTC125TKA / DTC125TSA

●Features

- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors.
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input, and parasitic effects are almost completely eliminated.
- 3) Only the on / off conditions need to be set for operation, making device design easy.
- 4) Higher mounting densities can be achieved.

●Circuit schematic



●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CB0}	50	—	—	V	I _C =50 μA
Collector-emitter breakdown voltage	BV _{CE0}	50	—	—	V	I _C =1mA
Emitter-base breakdown voltage	BV _{EB0}	5	—	—	V	I _E =50 μA
Collector cutoff current	I _{CB0}	—	—	0.5	μA	V _{CB} =50V
Emitter cutoff current	I _{EB0}	—	—	0.5	μA	V _{EB} =4V
Collector-emitter saturation voltage	V _{CE(sat)}	—	—	0.3	V	I _C =0.5mA, I _E =0.05mA
DC current transfer ratio	h _{FE}	100	250	600	—	I _C =1mA, V _{CE} =5V
Input resistance	R _I	70	100	130	kΩ	—
Transition frequency	f _T	—	250	—	MHz	V _{CE} =10V, I _E =-5mA, f=100MHz *

* Transition frequency of the device.

(94S-674-C125T)

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V _{CB0}	-50	V
Collector-emitter voltage	V _{CE0}	-50	V
Emitter-base voltage	V _{EB0}	-5	V
Collector current	I _C	-100	mA
Collector power dissipation	P _C	DTA125TUA / DTA125TKA	200
		DTA125TSA	300
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55~+150	°C

●Package, marking, and packaging specifications

Part No.	DTA125TUA	DTA125TKA	DTA125TSA
Package	UMT3	SMT3	SPT
Marking	9A	9A	—
Packaging code	T106	T146	TP
Basic ordering unit (pieces)	3000	3000	5000

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V _{CB0}	50	V
Collector-emitter voltage	V _{CE0}	50	V
Emitter-base voltage	V _{EB0}	5	V
Collector current	I _C	100	mA
Collector power dissipation	P _C	DTC125TUA / DTC125TKA	200
		DTC125TSA	300
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55~+150	°C

●Package, marking, and packaging specifications

Part No.	DTC125TUA	DTC125TKA	DTC125TSA
Package	UMT3	SMT3	SPT
Marking	0A	0A	—
Packaging code	T106	T146	TP
Basic ordering unit (pieces)	3000	3000	5000